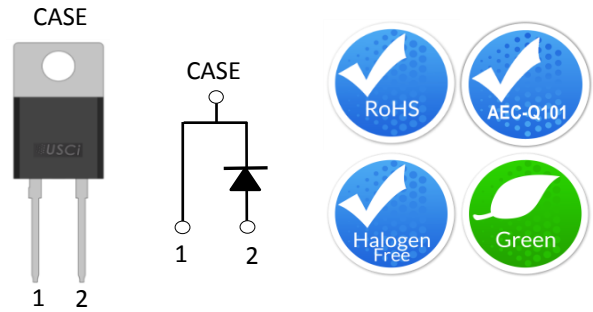


## Description

United Silicon Carbide, Inc. offers the 3<sup>rd</sup> generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D06520TS	TO-220-2L	UJ3D06520TS

## Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified

## Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

## Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	$V_R$		650	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	$V_{RRM}$		650	V
Surge peak reverse voltage	$V_{RSM}$		650	V
Maximum DC forward current	$I_F$	$T_C = 152^\circ\text{C}$	20	A
Non-repetitive forward surge current sine halfwave	$I_{FSM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	126	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	108	
Repetitive forward surge current sine halfwave, $D=0.1$	$I_{FRM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	83	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	52	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	820	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	820	
$i^2t$ value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	79.4	$\text{A}^2\text{s}$
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	58.3	
Power dissipation	$P_{Tot}$	$T_C = 25^\circ\text{C}$	272.7	W
		$T_C = 152^\circ\text{C}$	41.8	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	$T_J, T_{STG}$		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	$T_{sold}$	1.6mm from case for 10s	260	$^\circ\text{C}$

**Electrical Characteristics**

T<sub>J</sub> = +25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 20A, T <sub>J</sub> = 25°C	-	1.5	1.7	V
		I <sub>F</sub> = 20A, T <sub>J</sub> = 150°C	-	1.68	2.0	
		I <sub>F</sub> = 20A, T <sub>J</sub> = 175°C	-	1.75	2.1	
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 650V, T <sub>J</sub> = 25°C	-	20	120	μA
		V <sub>R</sub> = 650V, T <sub>J</sub> = 175°C	-	300		
Total capacitive charge <sup>(1)</sup>	Q <sub>C</sub>	V <sub>R</sub> = 400V		46		nC
Total capacitance	C	V <sub>R</sub> = 1V, f = 1MHz		654		pF
		V <sub>R</sub> = 300V, f = 1MHz		76		
		V <sub>R</sub> = 600V, f = 1MHz		68		
Capacitance stored energy	E <sub>C</sub>	V <sub>R</sub> = 400V		6.8		μJ

(1) Q<sub>C</sub> is independent on T<sub>J</sub>, di<sub>F</sub>/dt, and I<sub>F</sub> as shown in the application note USCi\_AN0011.

**Thermal characteristics**

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	R <sub>θJC</sub>			0.41	0.55	°C/W

**Typical Performance**

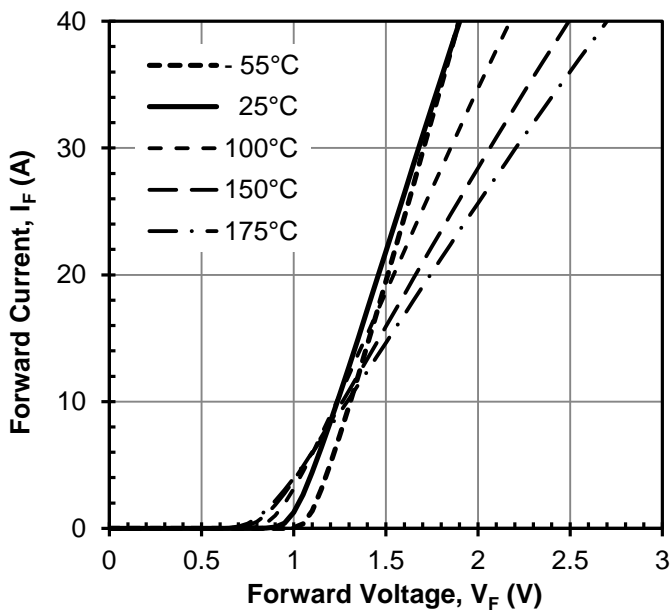


Figure 1 Typical forward characteristics

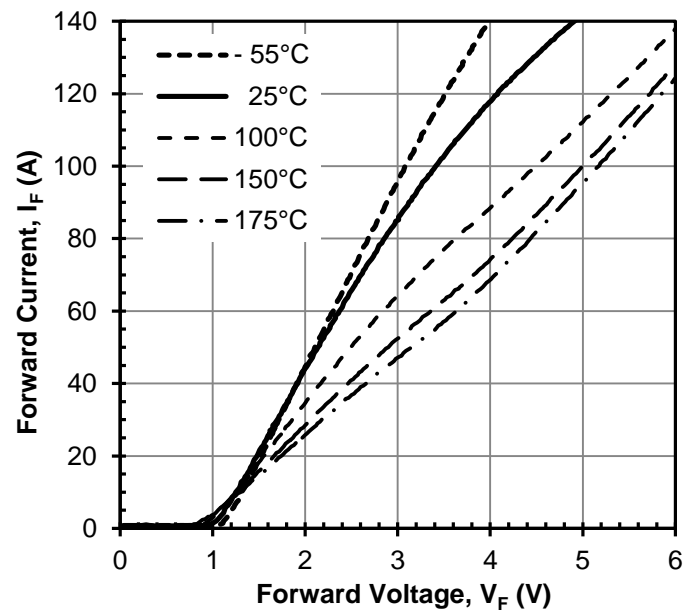


Figure 2 Typical forward characteristics in surge current

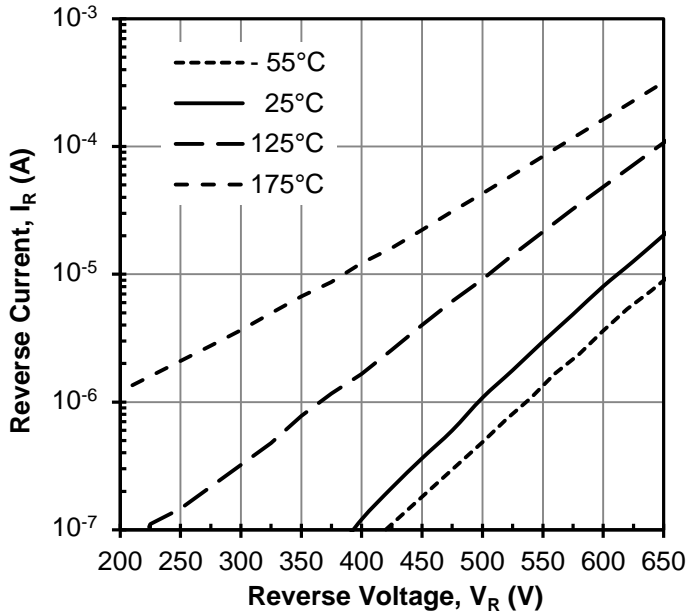


Figure 3 Typical reverse characteristics

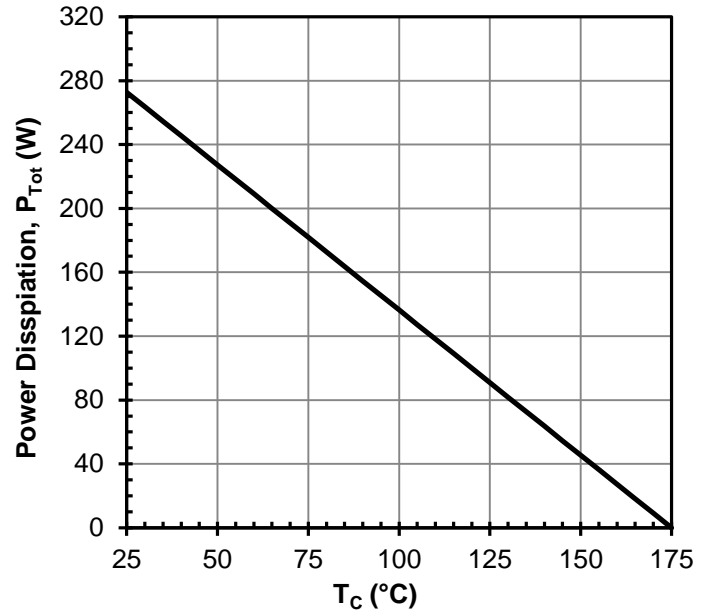


Figure 4 Power dissipation

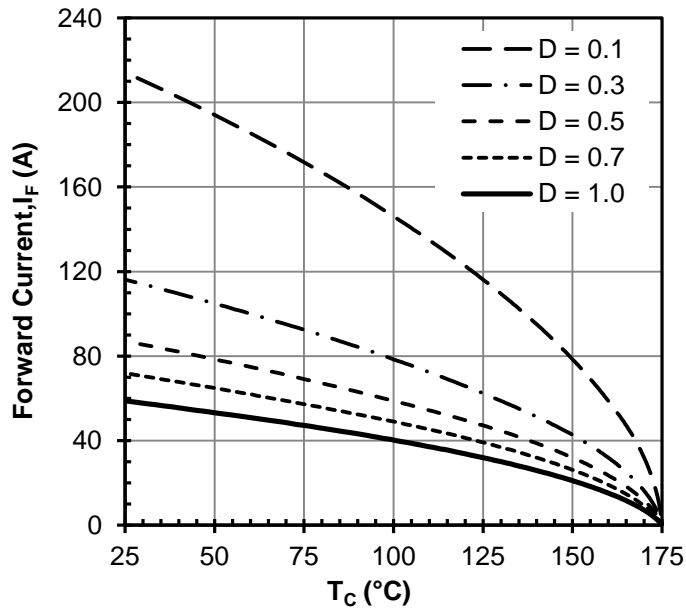


Figure 5 Diode forward current

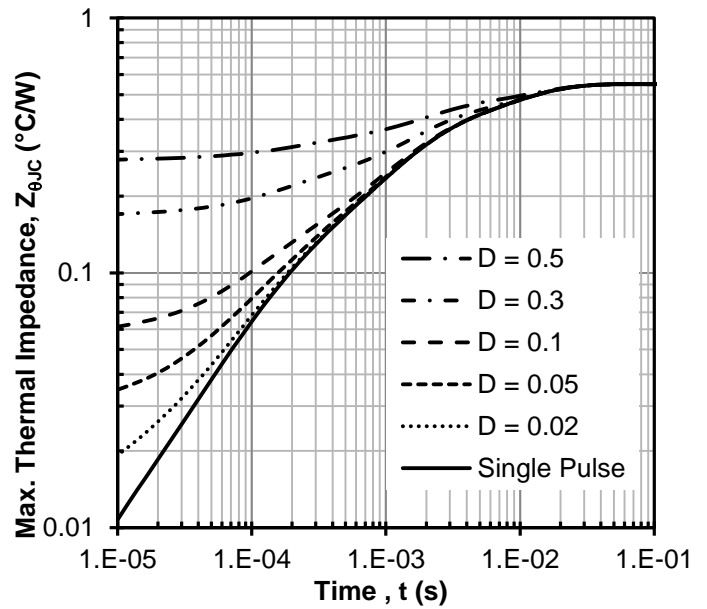
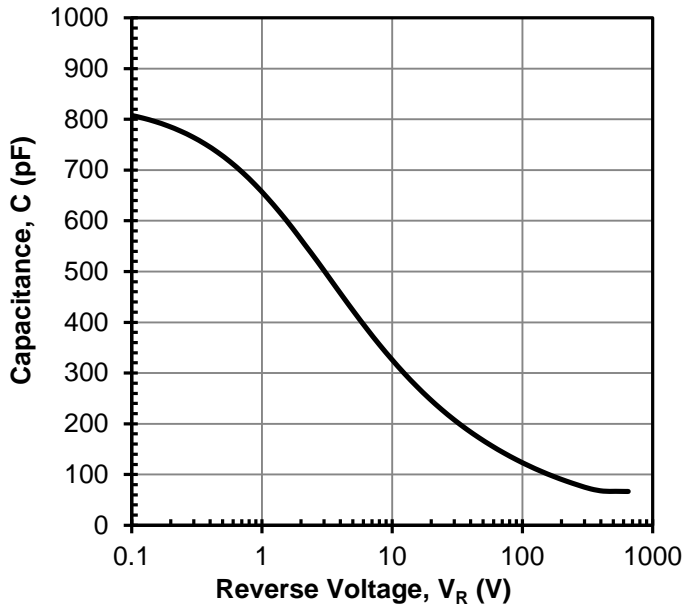
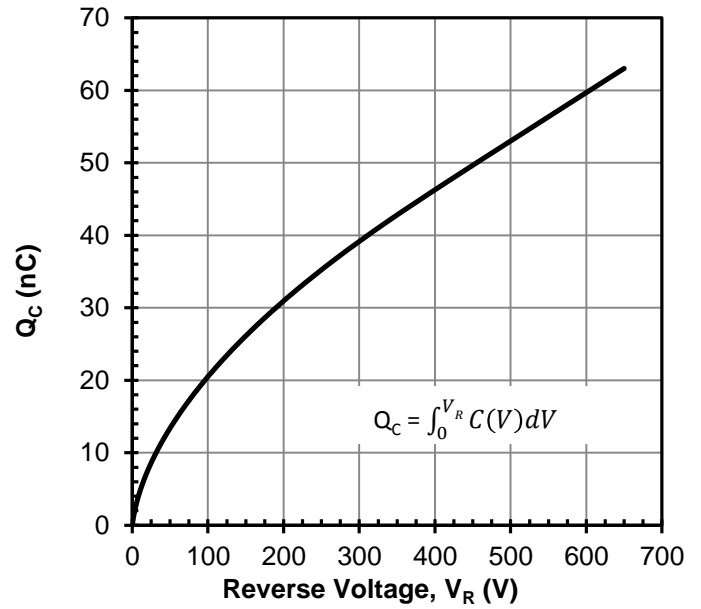


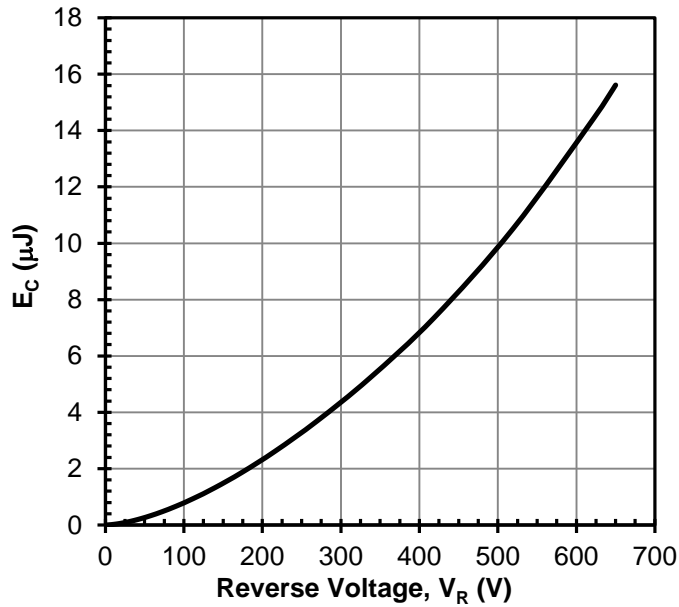
Figure 6 Maximum transient thermal impedance



**Figure 7** Capacitance vs. reverse voltage at 1MHz



**Figure 8** Typical capacitive charge vs. reverse voltage



**Figure 9** Typical capacitance stored energy vs. reverse voltage

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